

Serial No.09/975,297  
HP Docket No: 10007286-1

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In Re Application of:

Date: June 26, 2003

Viatcheslav Ossipov et al.

Serial No.:09/975,297

Group Art Unit: 2822

Filed: October 12, 2001

Examiner: Soward, Ida M.

For: HIGH CURRENT AVALANCHE-TUNNELING AND INJECTION  
TUNNELING SEMICONDUCTOR-DIELECTRIC-METAL STABLE  
COLD EMITTER, WHICH EMULATES THE NEGATIVE ELECTRON  
AFFINITY MECHANISM OF EMISSION

Honorable Commissioner of Patents and Trademarks  
Alexandria, VA 22313-1450

FAX RECEIVED

JUN 26 2003

TECHNOLOGY CENTER 2800

**RESPONSE TO OFFICE ACTION**

Sir:

In response to the Office Action dated March 27, 2003, please enter the following  
amendments and remarks into the above-identified application:

**AMENDMENTS**

Please amend the application in the following manner:

**IN THE CLAIMS**

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1. (Twice Amended) An electron emitter comprising:  
a p region;  
a dielectric layer formed directly above said p region;  
a metallic layer formed directly above said dielectric layer; and  
means for emitting electrons through said metallic layer.